

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications.

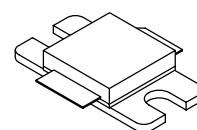
- Typical 2-carrier W-CDMA Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 450$ mA, $P_{out} = 11.5$ Watts Avg., $f = 2157$ MHz, Channel Bandwidth = 3.84 MHz, PAR = 8.5 dB @ 0.01% Probability on CCDF.
Power Gain — 16 dB
Drain Efficiency — 27.7%
IM3 @ 10 MHz Offset — -37 dBc in 3.84 MHz Channel Bandwidth
ACPR @ 5 MHz Offset — -40 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 2140 MHz, 50 Watts CW Output Power

Features

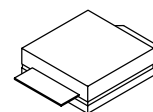
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 32 mm, 13 inch Reel.

MRF6S21050LR3
MRF6S21050LSR3

2110-2170 MHz, 11.5 W AVG., 28 V
2 x W-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465E-04, STYLE 1
NI-400
MRF6S21050LR3



CASE 465F-04, STYLE 1
NI-400S
MRF6S21050LSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +68	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +12	Vdc
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature (1,2)	T_J	225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		°C/W
Case Temperature 80°C, 50 W CW		1.16	
Case Temperature 76°C, 12 W CW		1.28	

- Continuous use at maximum temperature will affect MTTF.
- MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
- Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1C (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	III (Minimum)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 68\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 200\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage ($V_{DD} = 28\text{ Vdc}$, $I_D = 450\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	2	2.9	4	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 1.1\text{ Adc}$)	$V_{DS(on)}$	—	0.21	0.3	Vdc

Dynamic Characteristics ⁽¹⁾

Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	0.75	—	pF
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Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 450\text{ mA}$, $P_{out} = 11.5\text{ W Avg.}$, $f = 2157\text{ MHz}$, 2-carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset. IM3 measured in 3.84 MHz Bandwidth @ $\pm 10\text{ MHz}$ Offset. PAR = 8.5 dB @ 0.01% Probability on CCDF.

Power Gain	G_{ps}	15	16	18	dB
Drain Efficiency	η_D	26	27.7	—	%
Intermodulation Distortion	IM3	—	-37	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-40	-38	dBc
Input Return Loss	IRL	—	-15	-9	dB

1. Part is internally matched both on input and output.

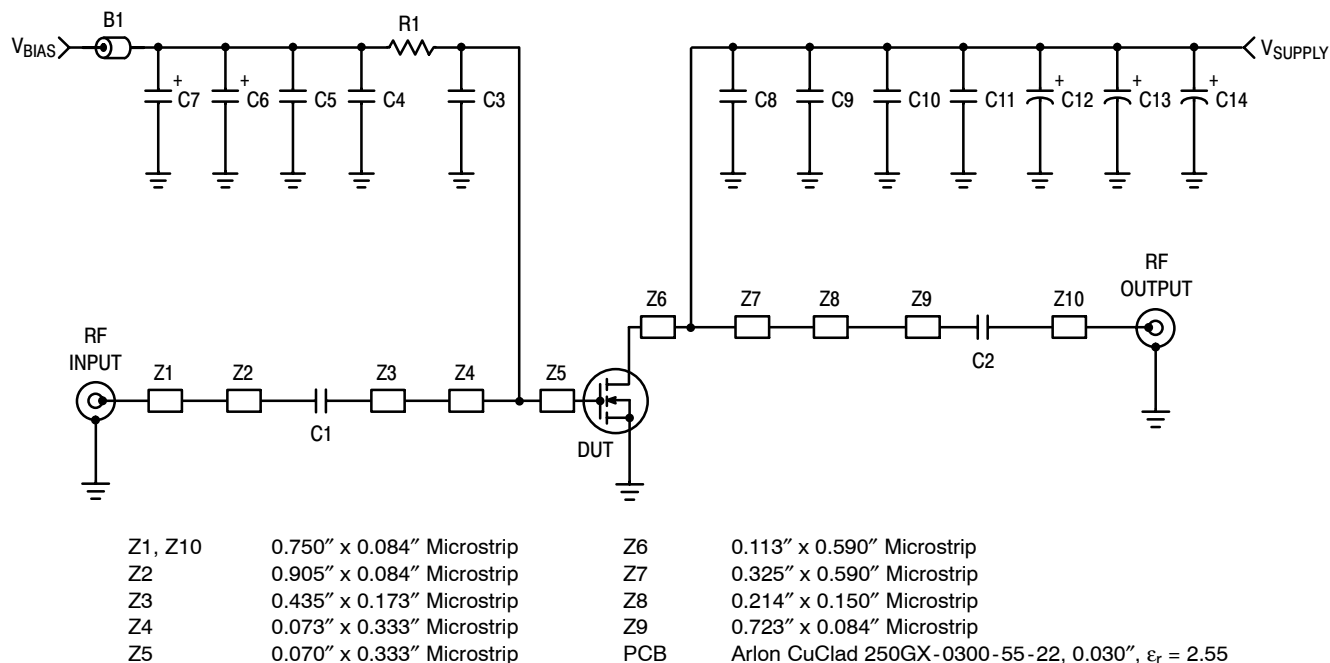
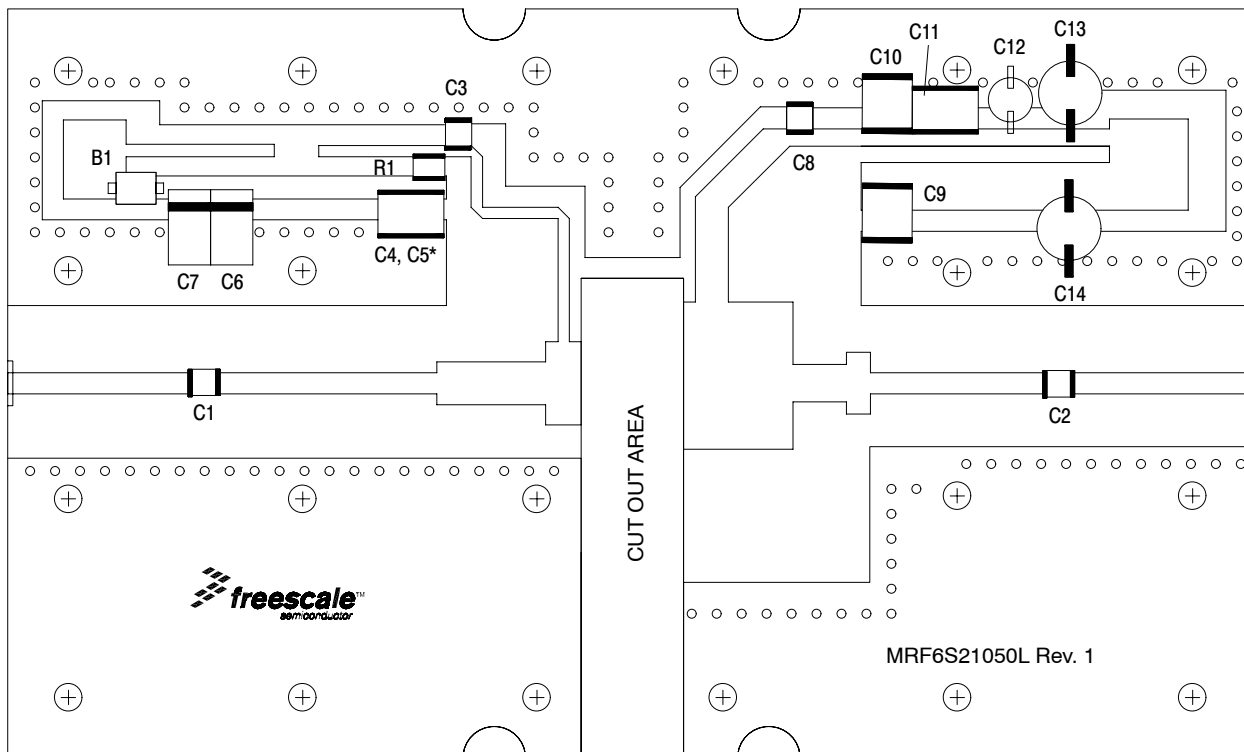


Figure 1. MRF6S21050LR3(LSR3) Test Circuit Schematic

Table 5. MRF6S21050LR3(LSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1	Bead, Surface Mount	2743019447	Fair-Rite
C1, C2, C3, C8	6.8 pF Chip Capacitors	ATC100B6R8CT500XT	ATC
C4	0.01 μ F Chip Capacitor	C1825C103J1RAC	Kemet
C5, C11	2.2 μ F, 50 V Chip Capacitors	C1825C225J5RAC	Kemet
C6	22 μ F, 25 V Tantalum Capacitor	T491D226K025AT	Kemet
C7	47 μ F, 16 V Tantalum Capacitor	T491D476K016AT	Kemet
C9, C10	10 μ F, 50 V Chip Capacitors	GRM55DR61H106KA88B	Murata
C12	47 μ F, 50 V Electrolytic Capacitor	EMVY500ADA470MF80G	Nippon
C13, C14	220 μ F, 50 V Electrolytic Capacitors	EMVY500ADA221MJA0G	Chem-Con
R1	3.3 Ω , 1/3 W Chip Resistor	CRCW12103R30FKEA	Vishay



* C4 on bottom, C5 on top.

Figure 2. MRF6S21050LR3(LSR3) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

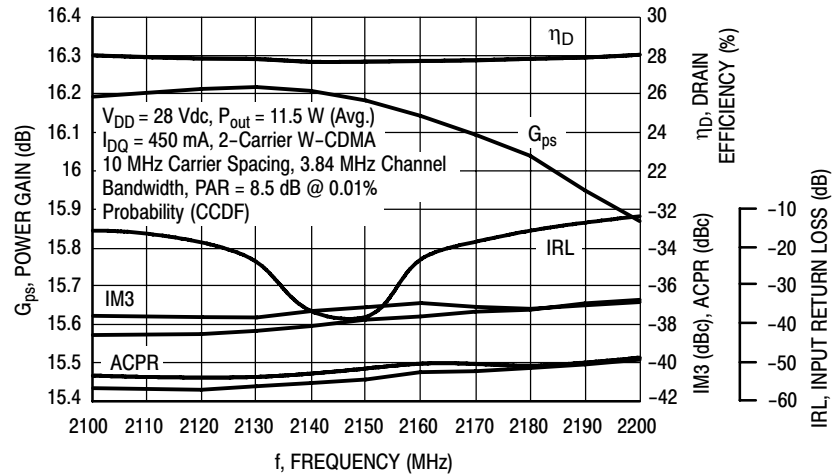


Figure 3. 2-Carrier W-CDMA Broadband Performance @ $P_{out} = 11.5 \text{ Watts}$

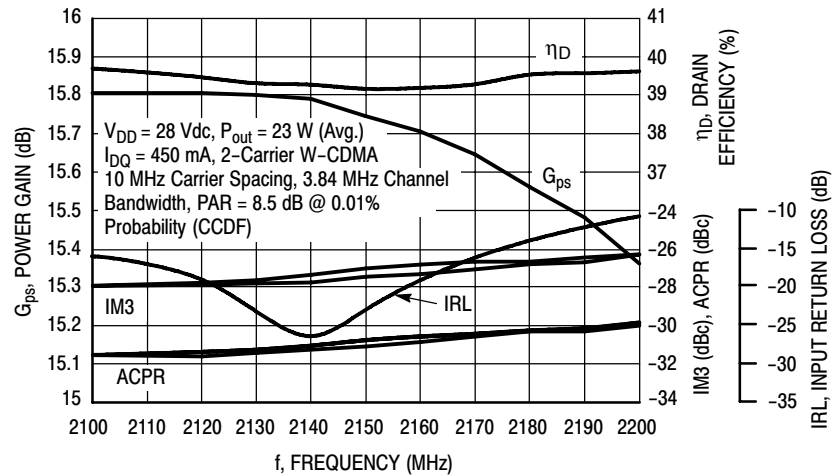


Figure 4. 2-Carrier W-CDMA Broadband Performance @ $P_{out} = 23 \text{ Watts}$

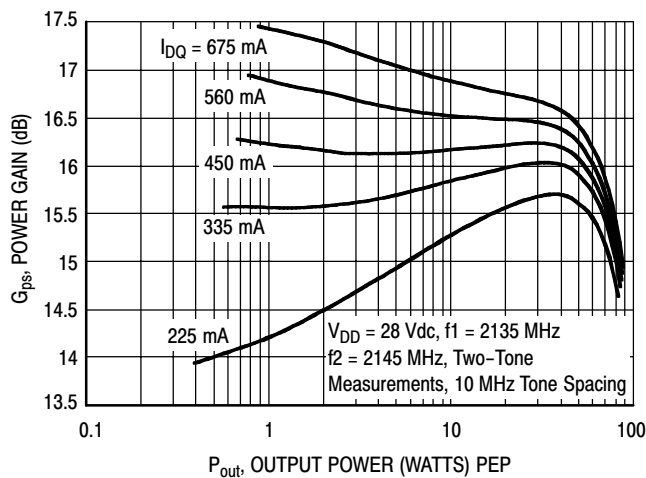


Figure 5. Two-Tone Power Gain versus Output Power

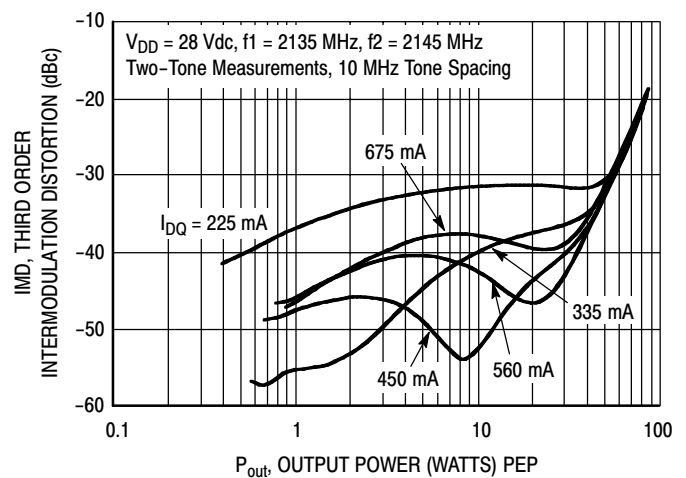


Figure 6. Third Order Intermodulation Distortion versus Output Power

TYPICAL CHARACTERISTICS

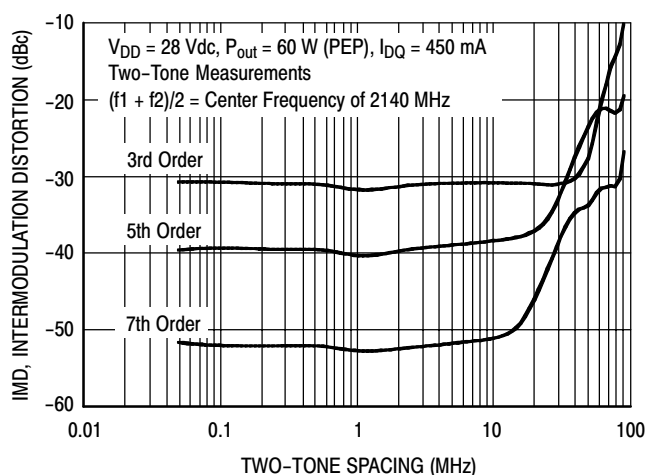


Figure 7. Intermodulation Distortion Products versus Tone Spacing

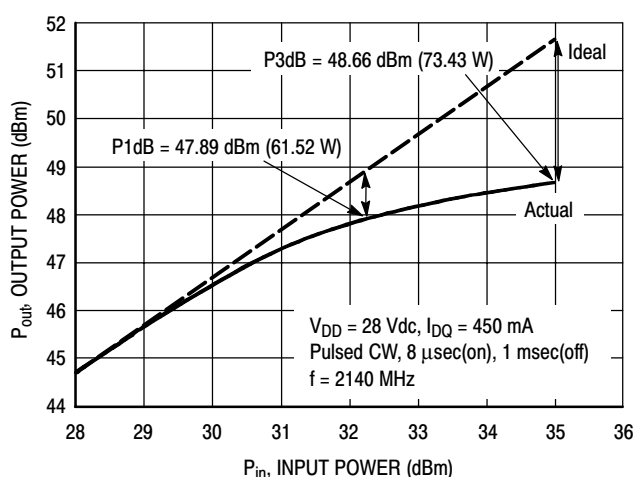


Figure 8. Pulsed CW Output Power versus Input Power

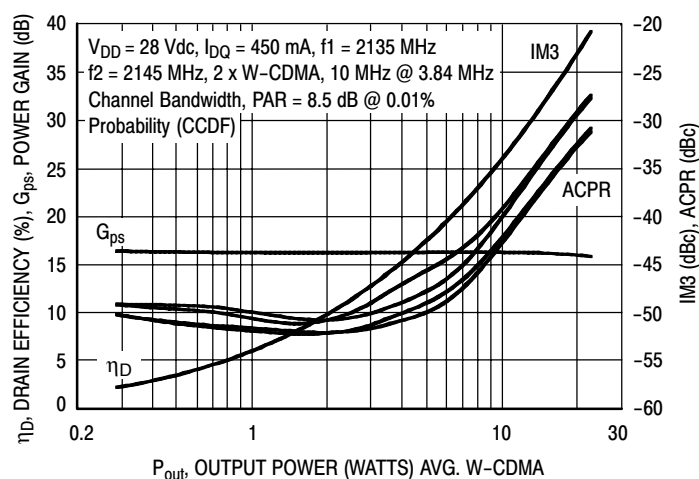


Figure 9. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

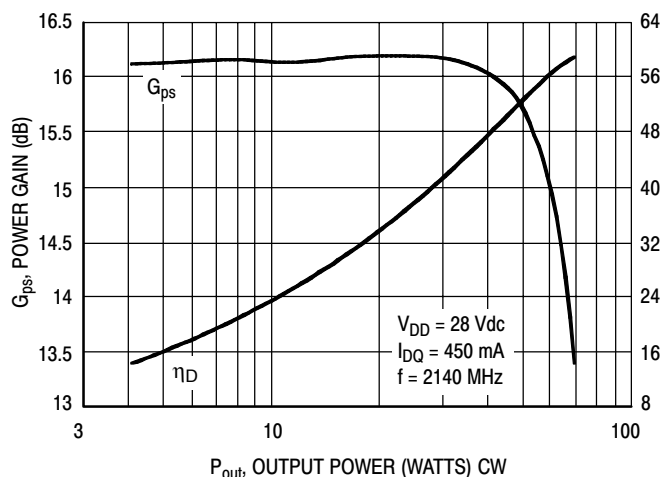


Figure 10. Power Gain and Drain Efficiency versus CW Output Power

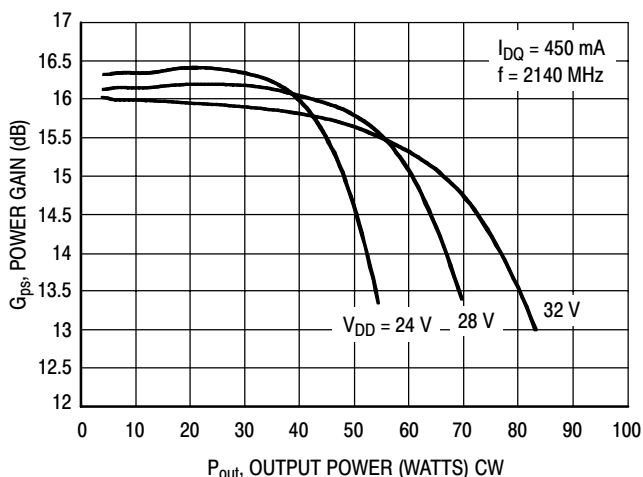
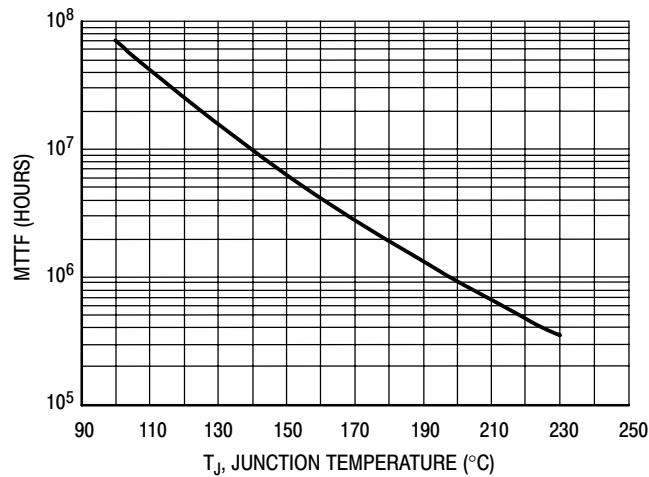


Figure 11. Power Gain versus Output Power

TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours when the device is operated at $V_{DD} = 28$ Vdc, $P_{out} = 11.5$ W Avg., and $\eta_D = 27.7\%$.

MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Figure 12. MTTF Factor versus Junction Temperature

W-CDMA TEST SIGNAL

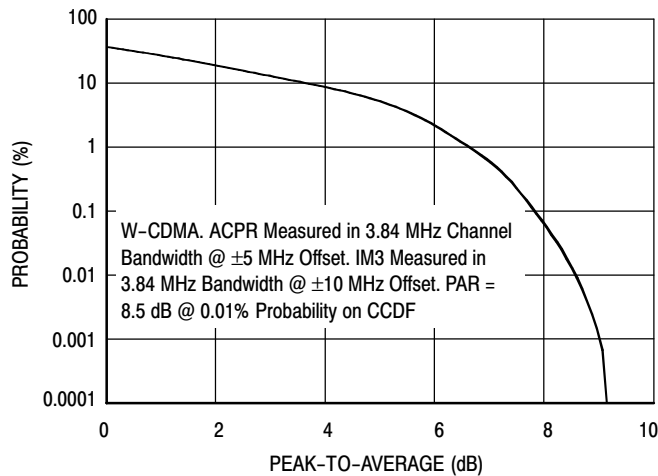


Figure 13. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 67% Clipping, Single-Carrier Test Signal

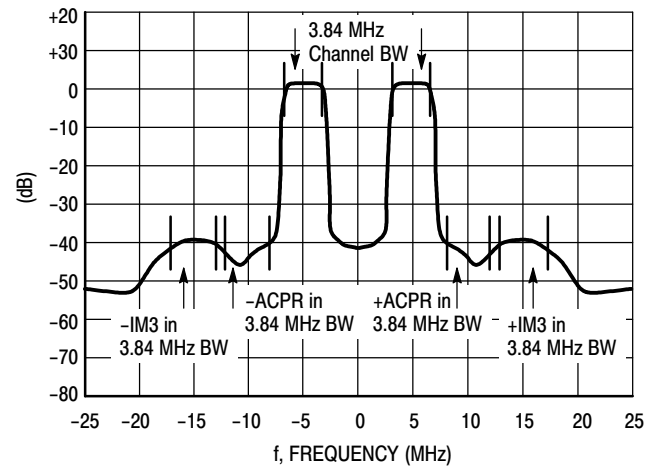
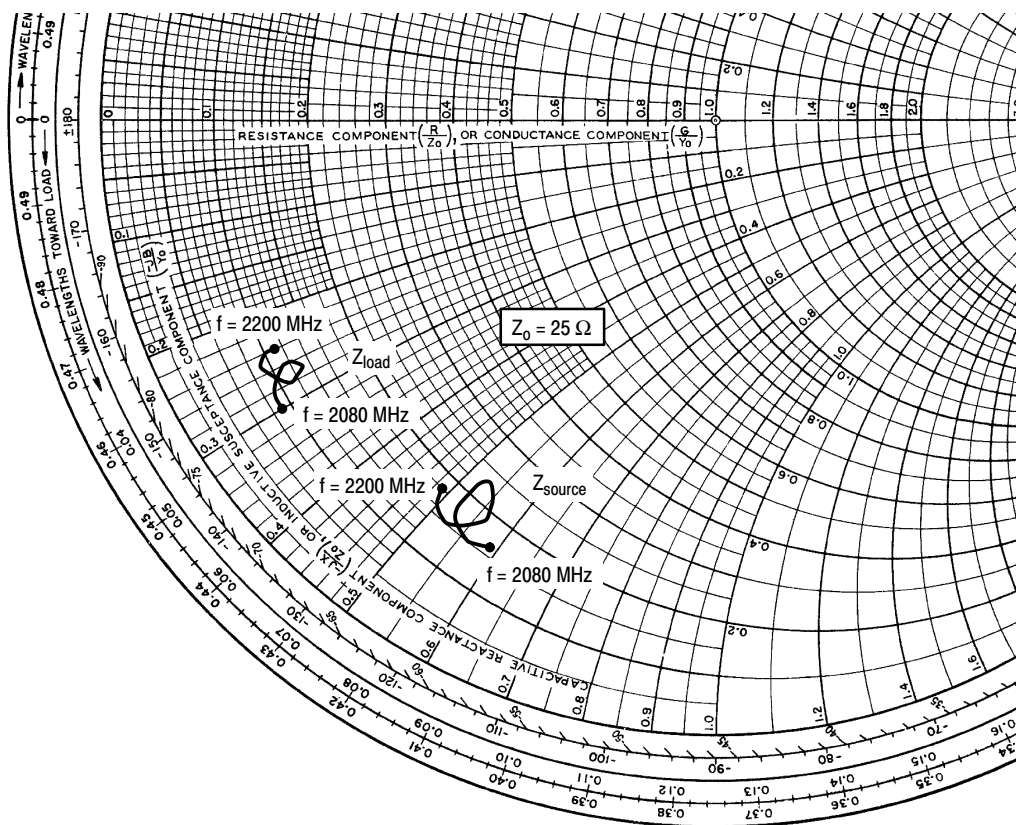


Figure 14. 2-Carrier W-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 450 \text{ mA}$, $P_{out} = 11.5 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
2080	4.09 - j14.65	2.36 - j7.52
2090	3.74 - j13.95	2.25 - j7.11
2100	3.95 - j13.36	2.40 - j6.78
2110	4.44 - j13.00	2.68 - j6.59
2120	5.03 - j12.89	2.99 - j6.52
2130	5.55 - j13.05	3.26 - j6.64
2140	5.76 - j13.26	3.32 - j6.68
2150	5.57 - j13.70	3.20 - j6.87
2160	4.86 - j13.92	2.82 - j6.93
2170	4.04 - j13.61	2.44 - j6.70
2180	3.69 - j12.91	2.33 - j6.29
2190	3.91 - j12.44	2.49 - j6.05
2200	4.41 - j12.32	2.77 - j5.96

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

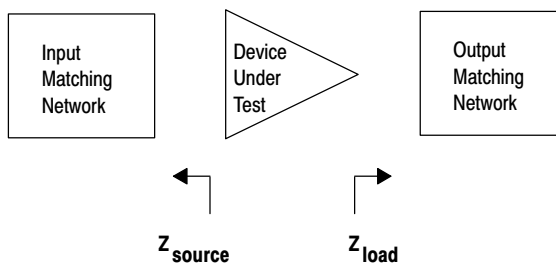
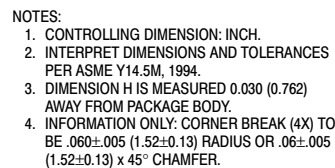
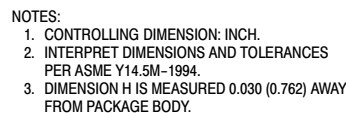


Figure 15. Series Equivalent Source and Load Impedance



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.795	.805	20.19	20.44
B	.380	.390	9.65	9.9
C	.125	.163	3.17	4.14
D	.275	.285	6.98	7.24
E	.035	.045	0.89	1.14
F	.004	.006	0.10	0.15
G	.600 BSC		15.24 BSC	
H	.057	.067	1.45	1.7
K	.092	.122	2.33	3.1
M	.395	.405	10	10.3
N	.395	.405	10	10.3
Q	Ø .120	Ø .130	Ø 3.05	Ø 3.3
R	.395	.405	10	10.3
S	.395	.405	10	10.3
aaa	.005 BSC		0.127 BSC	
bbb	.010 BSC		0.254 BSC	
ccc	.015 BSC		0.381 BSC	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.395	.405	10.03	10.29
B	.395	.405	10.03	10.29
C	.125	.163	3.18	4.14
D	.275	.285	6.98	7.24
E	.035	.045	0.89	1.14
F	.004	.006	0.10	0.15
H	.057	.067	1.45	1.70
K	.092	.122	2.34	3.10
M	.395	.405	10.03	10.29
N	.395	.405	10.03	10.29
R	.395	.405	10.03	10.29
S	.395	.405	10.03	10.29
aaa	.005 REF		0.127 REF	
bbb	.010 REF		0.254 REF	
ccc	.015 REF		0.38 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

RF Device Data
Freescale Semiconductor

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
2	Dec. 2008	• Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN13232, p. 1, 2 • Removed Low Gold Plating bullet from Features section as functionality is standard, p. 1 • Removed Total Device Dissipation from Max Ratings table as data was redundant (information already provided in Thermal Characteristics table), p. 1 • Operating Junction Temperature increased from 200°C to 225°C in Maximum Ratings table and related “Continuous use at maximum temperature will affect MTTF” footnote added, p. 1 • Corrected V_{DS} to V_{DD} in the RF test condition voltage callout for $V_{GS(Q)}$, and added “Measured in Functional Test”, On Characteristics table, p. 2 • Removed Forward Transconductance from On Characteristics table as it no longer provided usable information, p. 2 • Updated PCB information to show more specific material details, Fig. 1, Test Circuit Schematic, p. 3 • Updated Part Numbers in Table 5, Component Designations and Values, to latest RoHS compliant part numbers, p. 3 • Removed lower voltage tests from Fig. 11, Power Gain versus Output Power, due to fixed tuned fixture limitations, p. 6 • Replaced Fig. 12, MTTF versus Junction Temperature, with updated graph. Removed Amps² and listed operating characteristics and location of MTTF calculator for device, p. 7 • Added Product Documentation and Revision History, p. 10

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